

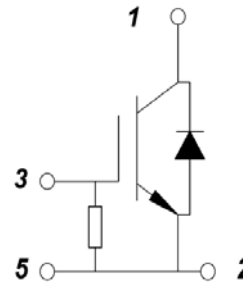
PRODUCT FEATURES

- IGBT3 CHIP(1700V Trench+Field Stop technology)
- Low turn-off losses, short tail current
- $V_{CE(sat)}$ with positive temperature coefficient
- DIODE CHIP(1700V EMCON 3 technology)
- Free wheeling diodes with fast and soft reverse recovery
- 5K Ω Gate Protected Resistance Inside



APPLICATIONS

- High frequency switching application
- Medical applications
- Motion/servo control
- UPS systems



IGBT-inverter

ABSOLUTE MAXIMUM RATINGS

$T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Values	t
V_{CES}	Collector Emitter Voltage	$T_J=25^\circ\text{C}$	1700	V
V_{GES}	Gate Emitter Voltage		± 20	
I_C	DC Collector Current	$T_C=25^\circ\text{C}$	800	A
		$T_C=90^\circ\text{C}$	600	
I_{CM}	Repetitive Peak Collector Current	$t_p=1\text{ms}$	1200	
P_{tot}	Power Dissipation Per IGBT		3300	W

Reverse-Diode

ABSOLUTE MAXIMUM RATINGS

$T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Values	t
V_{RRM}	Repetitive Reverse Voltage	$T_J=25^\circ\text{C}$	1700	V
$I_{F(AV)}$	Average Forward Current	$T_C=25^\circ\text{C}$	600	A
I_{FRM}	Repetitive Peak Forward Current	$t_p=1\text{ms}$	1200	
I^2t		$T_J=125^\circ\text{C}$, $t=10\text{ms}$, $V_R=0\text{V}$	57000	A^2S

IGBT-inverter
ELECTRICAL CHARACTERISTICS
 $T_C=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	t	
$V_{GE(th)}$	Gate Emitter Threshold Voltage	$V_{CE}=V_{GE}, I_C=24\text{mA}$	5.2	5.8	6.4	V	
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$I_C=600\text{A}, V_{GE}=15\text{V}, T_J=25^{\circ}\text{C}$		2	2.45		
		$I_C=600\text{A}, V_{GE}=15\text{V}, T_J=125^{\circ}\text{C}$		2.4			
I_{CES}	Collector Leakage Current	$V_{CE}=1700\text{V}, V_{GE}=0\text{V}, T_J=25^{\circ}\text{C}$			3	mA	
		$V_{CE}=1700\text{V}, V_{GE}=0\text{V}, T_J=125^{\circ}\text{C}$			20	mA	
I_{GES}	Gate Leakage Current	$V_{CE}=0\text{V}, V_{GE}=\pm 15\text{V}, T_J=125^{\circ}\text{C}$	-400		400	nA	
R_{gint}	Integrated Gate Resistor			1.3		Ω	
Q_g	Gate Charge	$V_{CE}=900\text{V}, I_C=600\text{A}, V_{GE}=\pm$		7		μC	
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$		54		nF	
C_{res}	Reverse Transfer Capacitance				1.8		nF
$t_{d(on)}$	Turn on Delay Time	$V_{CC}=900\text{V}, I_C=600\text{A}$ $R_G=2.4\Omega,$ $V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^{\circ}\text{C}$		380		ns
			$T_J=125^{\circ}\text{C}$		420		ns
t_r	Rise Time		$T_J=25^{\circ}\text{C}$		100		ns
			$T_J=125^{\circ}\text{C}$		120		ns
$t_{d(off)}$	Turn off Delay Time	$V_{CC}=900\text{V}, I_C=600\text{A}$ $R_G=2.4\Omega,$ $V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^{\circ}\text{C}$		900		ns
			$T_J=125^{\circ}\text{C}$		1100		ns
t_f	Fall Time		$T_J=25^{\circ}\text{C}$		180		ns
			$T_J=125^{\circ}\text{C}$		300		ns
E_{on}	Turn on Energy	$V_{CC}=900\text{V}, I_C=600\text{A}$ $R_G=2.4\Omega,$ $V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^{\circ}\text{C}$		142		mJ
			$T_J=125^{\circ}\text{C}$		210		mJ
E_{off}	Turn off Energy		$T_J=25^{\circ}\text{C}$		128		mJ
			$T_J=125^{\circ}\text{C}$		188		mJ
I_{sc}	Short Circuit Current	$t_{psc}\leq 10\mu\text{S}, V_{GE}=15\text{V}$ $T_J=125^{\circ}\text{C}, V_{CC}=1000\text{V}$		2400		A	
R_{thJC}	Junction to Case Thermal Resistance (Per IGBT)				0.045	K/W	

Reverse-Diode
ELECTRICAL CHARACTERISTICS
 $T_C=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	t
V_F	Forward Voltage	$I_F=600\text{A}, V_{GE}=0\text{V}, T_J=25^{\circ}\text{C}$		1.8	2.2	V
		$I_F=600\text{A}, V_{GE}=0\text{V}, T_J=125^{\circ}\text{C}$		1.9		
I_{RRM}	Max. Reverse Recovery Current	$I_F=600\text{A}, V_R=900\text{V}$		700		A
Q_{RR}	Reverse Recovery Charge	$di_F/dt=-6000\text{A}/\mu\text{s}$		255		μC
E_{rec}	Reverse Recovery Energy	$T_J=125^{\circ}\text{C}$		150		mJ
R_{thJCD}	Junction to Case Thermal Resistance (Per Diode)				0.075	K/W

MODULE CHARACTERISTICS

$T_C=25^{\circ}\text{C}$ unless otherwise sp

Symbol	Parameter/Test Conditions		Values	t
T_{Jmax}	Max. Junction Temperature		175	°C
T_{Jop}	Operating Temperature		-40~150	
T_{stg}	Storage Temperature		-40~125	
V_{isol}	Isolation Breakdown Voltage	AC, 50Hz(R.M.S), t=1minute	4000	V
Torque	to heatsink	Recommended (M6)	3~5	Nm
	to terminal	Recommended (M6)	2.5~5	Nm
	to terminal	Recommended (M4)	0.7~1.1	Nm
Weight			330	g

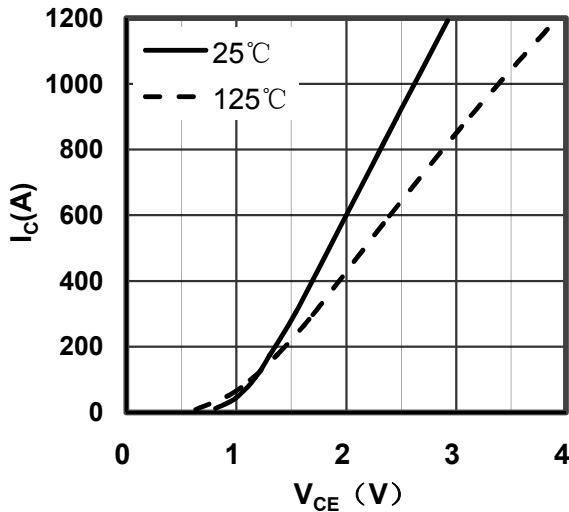


Figure 1. Typical Output Characteristics IGBT-inverter

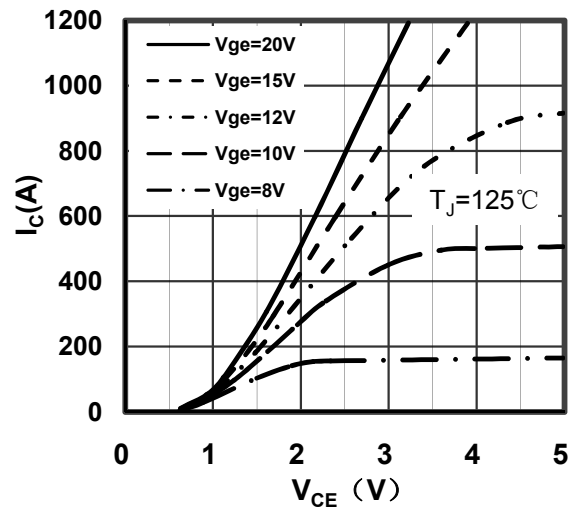


Figure 2. Typical Output Characteristics IGBT-inverter

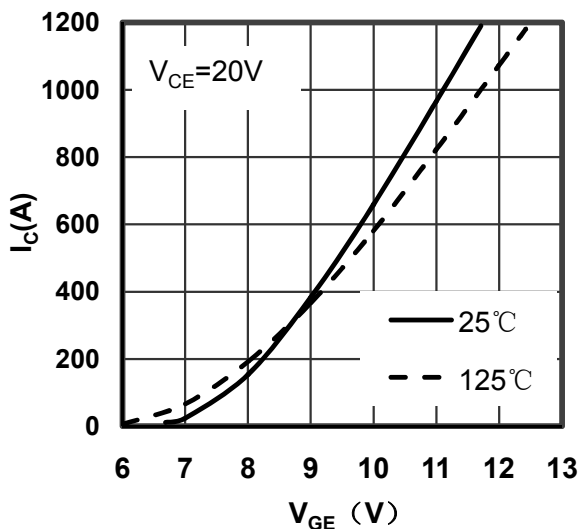


Figure 3. Typical Transfer Characteristics IGBT-inverter

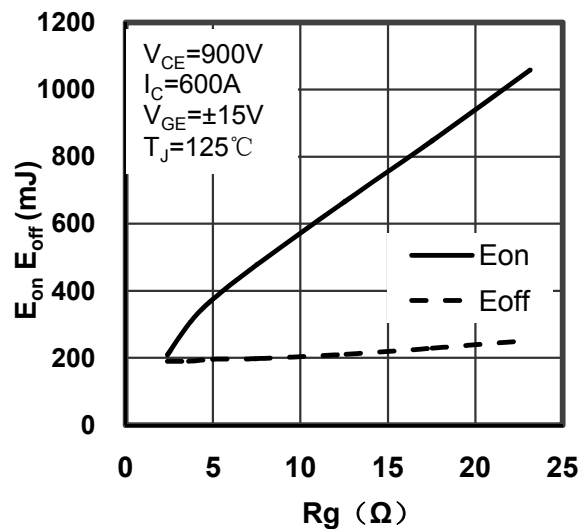


Figure 4. Switching Energy vs Gate Resistor IGBT-inverter

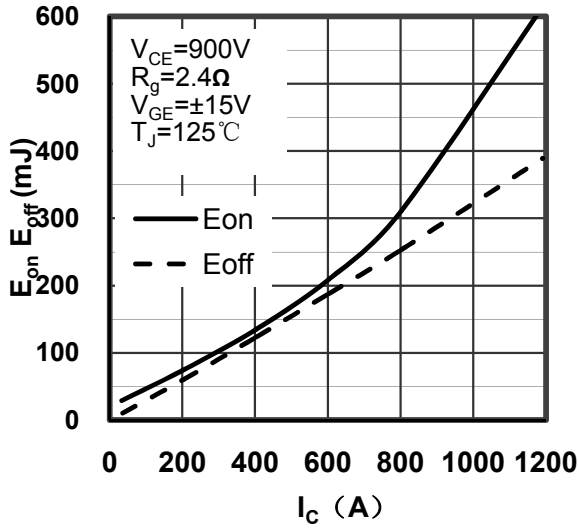


Figure 5. Switching Energy vs Collector Current IGBT-inverter

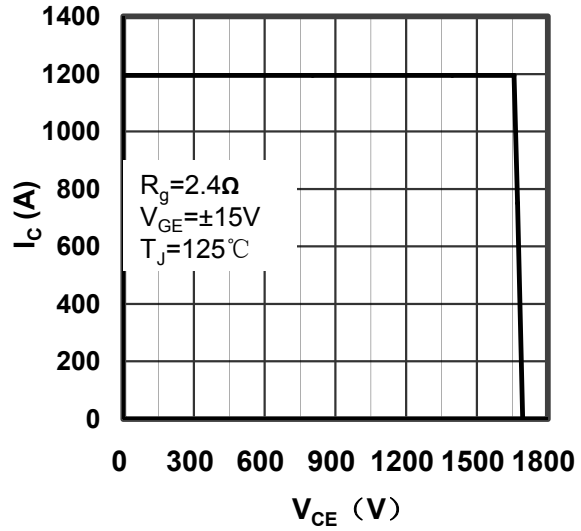


Figure 6. Reverse Biased Safe Operating Area IGBT-inverter



Figure 7. Collector Current vs Case temperature IGBT -inverter

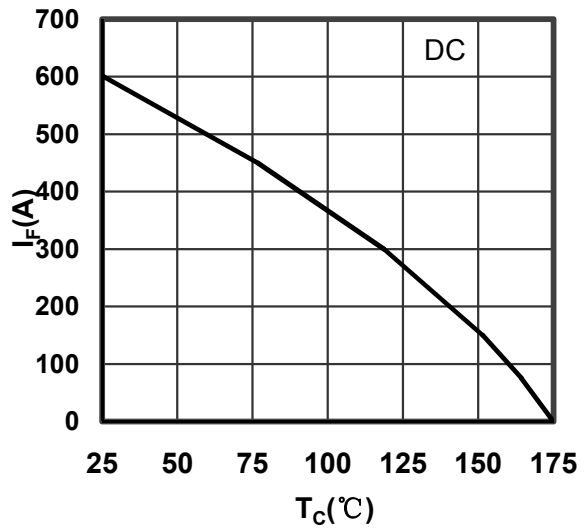


Figure 8. Forward current vs Case temperature Reverse-Diode

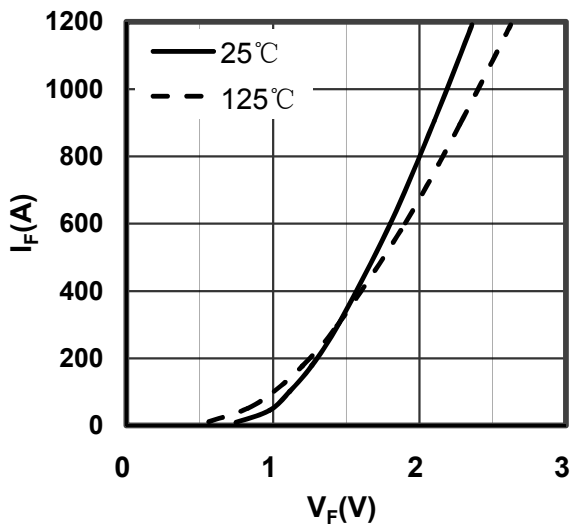


Figure 9. Diode Forward Characteristics Reverse-Diode

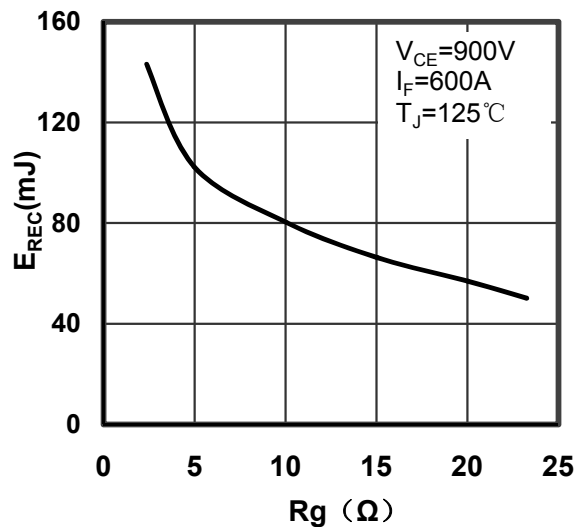


Figure 10. Switching Energy vs Gate Resistor Reverse-Diode

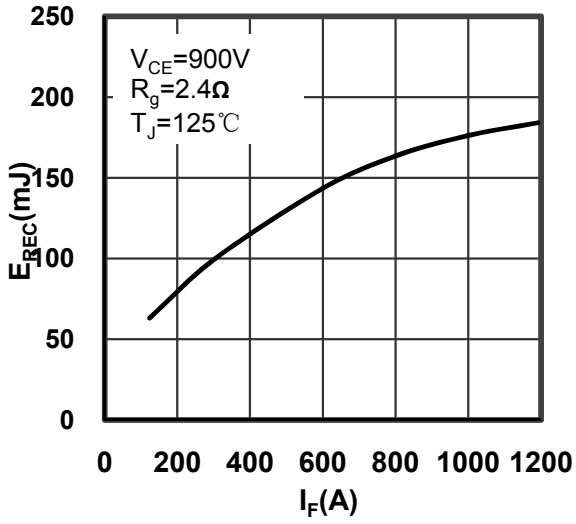


Figure 11. Switching Energy vs Forward Current Reverse-Diode

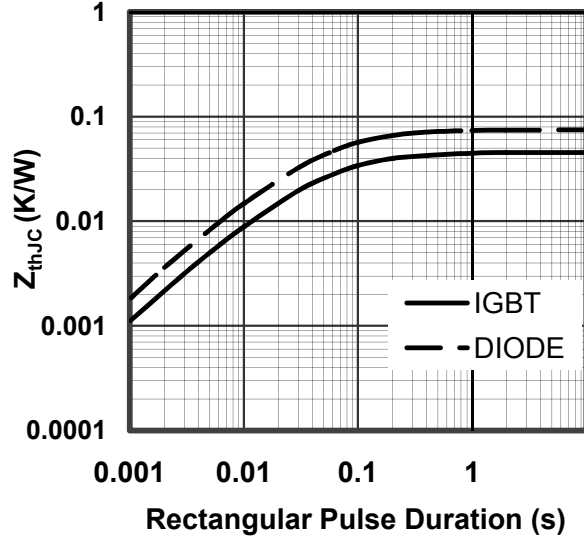
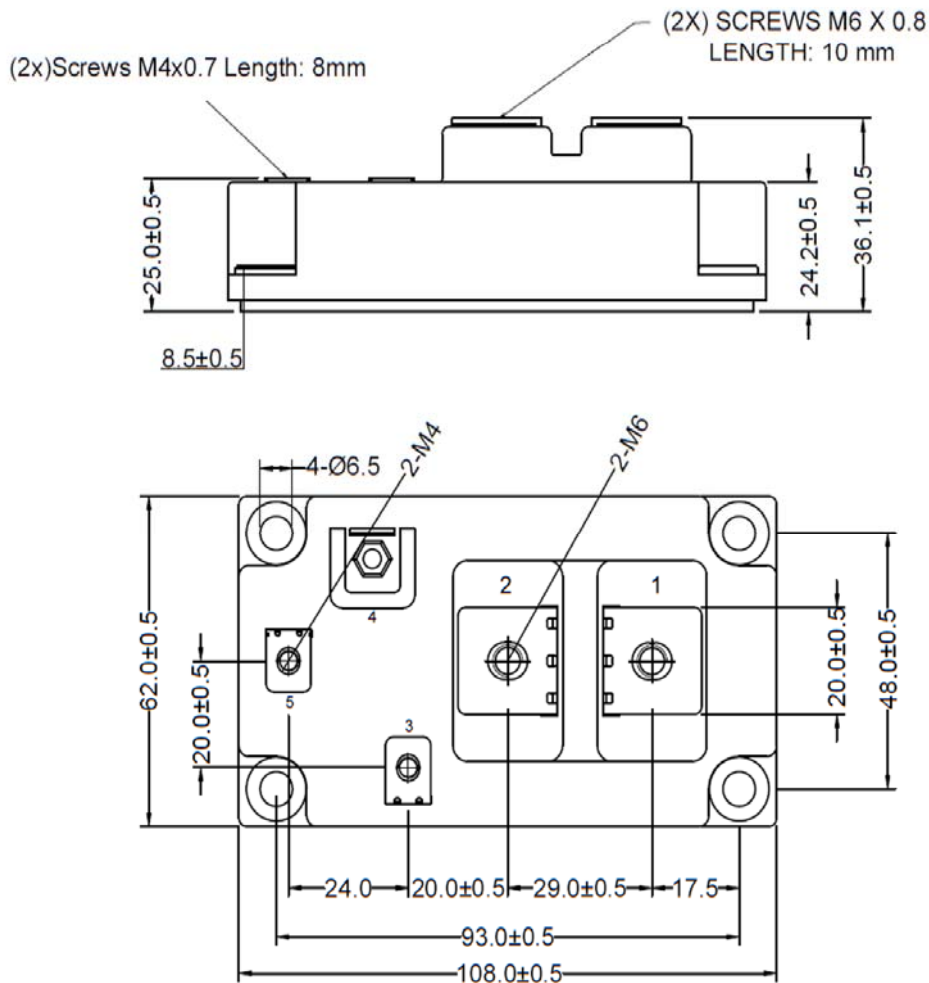


Figure 12. Transient Thermal Impedance of Reverse-Diode and IGBT-inverter



Dimensions in (mm)
Figure 13. Package Outline